Product data sheet

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT78 (T0-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

3. Applications

- General purpose phase control
- General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	-	155	A
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	16	A
Static chara	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	2.5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	4	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	5	10	mA





4Q Triac

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2- G+;	-	11	25	mA
		T _j = 25 °C; <u>Fig. 7</u>				

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2	 	sym051
3	G	gate		
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BT139-800E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78		

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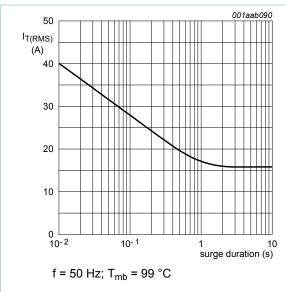
7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$; Fig. 2; Fig. 3	-	16	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	155	A
		full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$	-	170	Α
I ² t	I2t for fusing	t _p = 10 ms; SIN	-	120	A ² s
dI _T /dt	rate of rise of on-state current	I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G+	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

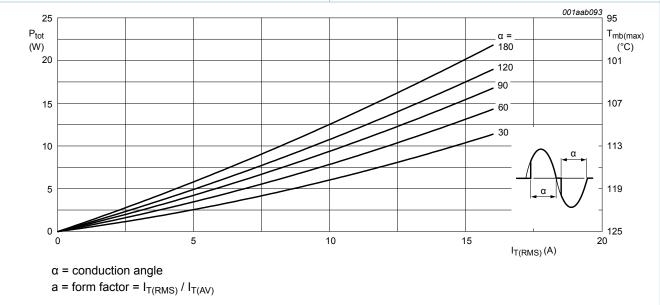
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20 001aab091 1T(RMS) (A) (1) 15 10 10 150 T_{mb} (°C) (1) T_{mb} = 99 °C

Fig. 1. RMS on-state current as a function of surge duration; maximum values

Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



4/13

4Q Triac

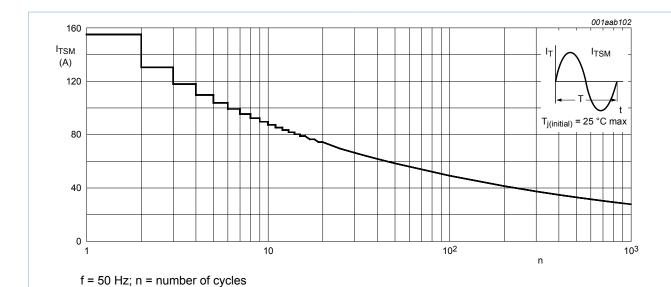
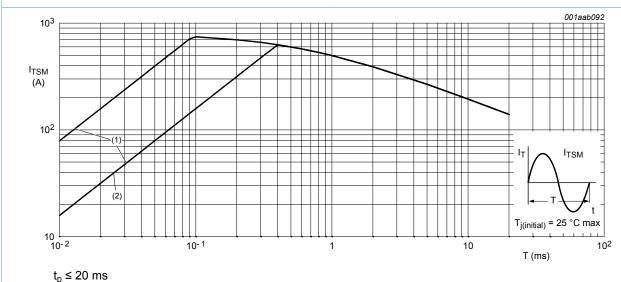


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



τ_p = 20 ms

(1) dI_T/dt limit

(2) T2- G+ quadrant limit

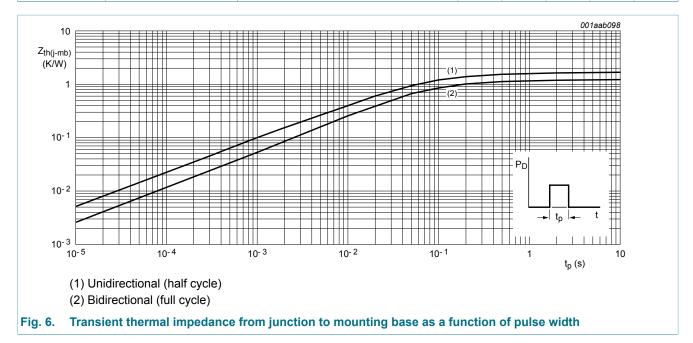
Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	half cycle; Fig. 6	-	-	1.7	K/W
	from junction to mounting base	full cycle; Fig. 6	-	-	1.2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



4Q Triac

9. Characteristics

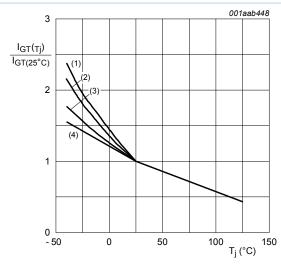
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	2.5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	4	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	11	25	mA
L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	3.2	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 ^{\circ}\text{C}; \text{Fig. 8}$	-	16	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$	-	4	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$	-	5.5	40	mA
Ін	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	4	45	mA
V _T	on-state voltage	I _T = 20 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.6	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
l _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic c	characteristics		l l			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 20 A; V_D = 800 V; I_G = 0.1 A; dI_G/dt = 5 A/ μ s	-	2	-	μs

Product data sheet

7/13

4Q Triac



- (1) T2- G+
- (2) T2+ G-
- (3) T2- G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

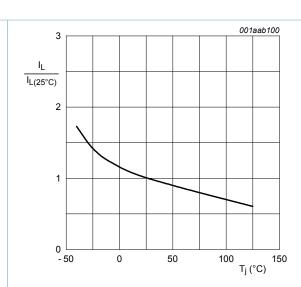


Fig. 8. Normalized latching current as a function of junction temperature

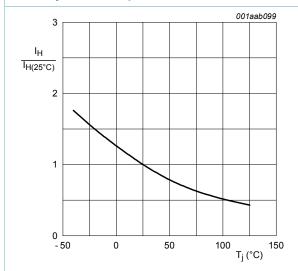
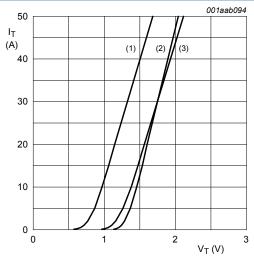


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 1.195 V; R_s = 0.018 Ω

- (1) T_i = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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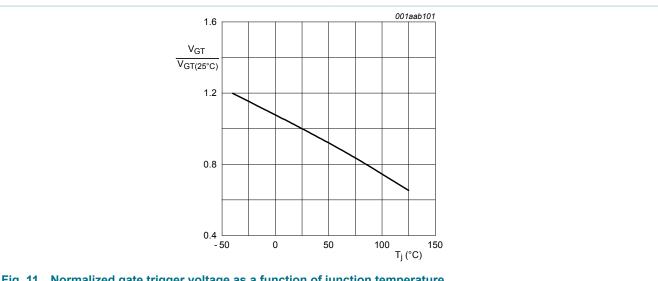
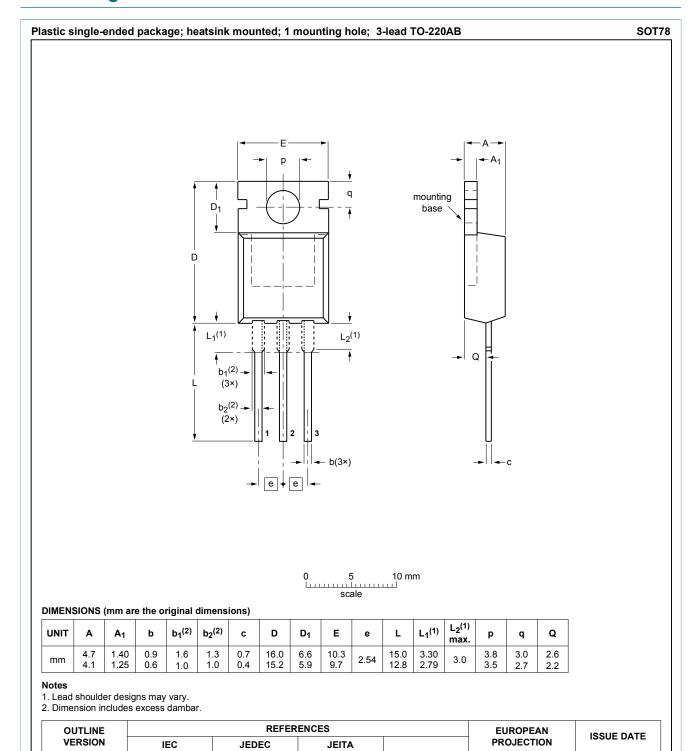


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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10. Package outline



SOT78 3-lead TO-220AB

Fig. 12. Package outline TO-220AB (SOT78)

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10 / 13

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11. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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12. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Limiting values	3
8	Thermal characteristics	
9	Characteristics	7
10	Package outline	10
11	Legal information	11
11.1	Data sheet status	11
11.2	Definitions	11
11.3	Disclaimers	11
11.4	Trademarks	12

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